Spread Spectrum Clock Generator

MB88162

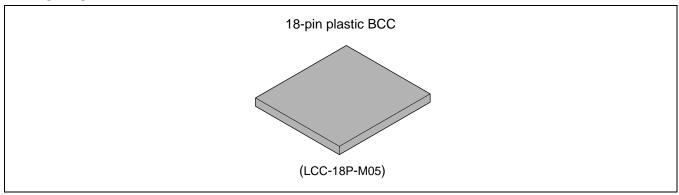
■ DESCRIPTION

MB88162 is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary radiation noise (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator.

■ FEATURES

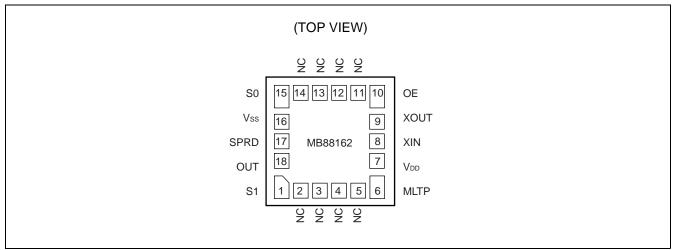
- Input frequency: 12 MHz to 28 MHz (Multiplied by 1), 20 MHz to 42 MHz (Multiplied by 4)
- Multiplication rate: 1, 4
- Output frequency: 12 MHz to 28 MHz (Multiplied by 1), 80 MHz to 168 MHz (Multiplied by 4)
- Modulation rate: no modulation, $\pm 0.5\%$, $\pm 1.0\%$, $\pm 2.0\%$, -1.0%, -2.0%, -4.0% (The terminal can be selected.)
- Equipped with oscillation circuit: Range of oscillation 12 MHz to 42 MHz
- Built-in oscillation stabilization capacitance : 4 pF (Typ)
- Modulation clock output Duty: 40% to 60%
- Modulation clock Cycle-Cycle Jitter: Less than 100 ps
- Low power consumption by CMOS process: 7.0 mA (24 MHz: no load, Typ-sample, Typ-condition)
- Power supply voltage: 2.7 V to 3.6 V (Multiplied by 1), 3.0 V to 3.6 V (Multiplied by 4)
- Operating temperature : $-40 \, ^{\circ}\text{C}$ to $+85 \, ^{\circ}\text{C}$
- Package : BCC 18-pin

■ PACKAGE





■ PIN ASSIGNMENT



■ PIN DESCRIPTION

Pin no.	Pin name	I/O	Description	
1	S1	I	Modulation rate setting pin (with pull-up resistance)	
2	NC	_	Non-connection pin (do not connect anything)	
3	NC	_	Non-connection pin (do not connect anything)	
4	NC	_	Non-connection pin (do not connect anything)	
5	NC	_	Non-connection pin (do not connect anything)	
6	MLTP	I	Multiplication rate setting pin (with pull-down resistance)	
7	V _{DD}	_	Power supply voltage pin	
8	XIN	Ţ	Resonator connection pin/clock input pin	
9	XOUT	0	Resonator connection pin	
10	OE	I	Clock output enable pin (with pull-up resistance)	
11	NC	_	Non-connection pin (do not connect anything)	
12	NC	_	Non-connection pin (do not connect anything)	
13	NC	_	Non-connection pin (do not connect anything)	
14	NC	_	Non-connection pin (do not connect anything)	
15	S0	Ţ	Modulation rate setting pin (with pull-up resistance)	
16	Vss	_	GND pin	
17	SPRD	I	Modulation type setting pin (with pull-up resistance)	
18	OUT	0	Modulation clock output pin (OE= "L" Hi-Z output)	

■ I/O CIRCUIT TYPE

Pin	Circuit type	Remarks
OE	$\begin{array}{c} 22 \text{ k}\Omega \\ \text{OE signal} \\ \\ \text{Note : At OE="L"} \\ 22 \text{k}\Omega \\ \text{Pull Up cut} \\ \end{array}$	 With pull-up resistor The value of pull-up resistor is switched by the input level of OE signal. 800 kΩ at OE= "L" (Typ) 22 kΩ at OE= "H" (Typ) CMOS hysteresis input
S0, S1, SPRD	OE signal Note: At OE="L" Pull Up cut	 With pull-up resistor 50 kΩ (Typ) CMOS hysteresis input Pull-up resistor is disconnected at OE= "L", and internal signal is fixed to "L".
MLTP	OE signal 50 kΩ Note: At OE="L" Pull Down cut	 With pull-down resistor 50 kΩ (Typ) CMOS hysteresis input Pull-down resistor is disconnected at OE= "L", and internal signal is fixed to "L".
OUT	OE signal Note: At OE="L" Hi-Z output	 CMOS output IoL = 8.0 mA Hi-Z output at OE = "L"

(Continued)

Pin	Circuit type	Remarks
XIN, XOUT	XIN $\begin{picture}(20,5) \put(0,0){\line(1,0){100}} \put(0,0){\line(1,0$	 Oscillation circuit Built-in feedback resistance: 500 kΩ (Typ) Built-in oscillation stabilization capacitance: 4 pF (Typ)

■ HANDLING DEVICES

Preventing Latch-up

A latch-up can occur if, on this device, (a) a voltage higher than power supply voltage or a voltage lower than GND is applied to an input or output pin or (b) a voltage higher than the rating is applied between power supply and GND. The latch-up, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

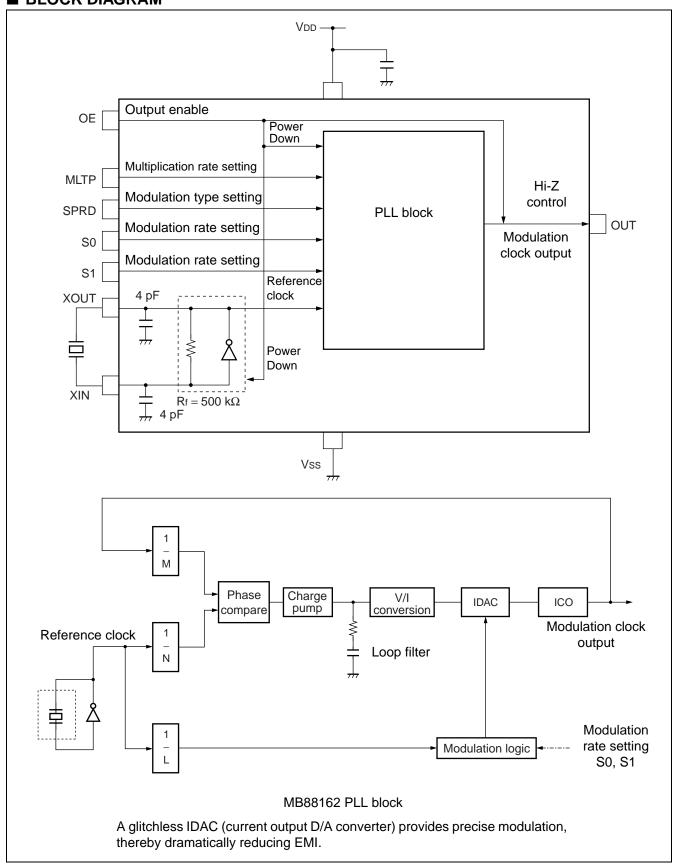
We recommend connecting electrolytic capacitor (about 10 μ F) and the ceramic capacitor (about 0.01 μ F) in parallel between power supply and GND near the device, as a bypass capacitor.

Oscillation circuit

Noise near the XIN pin and XOUT pin may cause the device to malfunction. Design printed circuit boards so that electric wiring of XIN pin or XOUT pin and the resonator do not intersect other wiring.

Design the printed circuit board that surrounds the XIN pin and XOUT pin with ground.

■ BLOCK DIAGRAM



■ PIN SETTING

After the pin setting is changed, the stabilization wait time of the modulation clock is required. The stabilization wait time of the modulation clock takes the maximum value of Lock-Up time in "• AC Characteristics" in

■ ELECTRICAL CHARACTERISTICS.

Each setting pin contains the pull-up resistor or pull-down resistor. Therefore, these pins is set to default state for input opened.

MLTP multiplication setting

MLTP	Multiplication rate	Input Frequency	Output Frequency	Remarks
L	Multiplied by 1	12 MHz to 28 MHz	12 MHz to 28 MHz	Default
Н	Multiplied by 4	20 MHz to 42 MHz	80 MHz to 168 MHz	_

Note: Set MLTP pin to "L" for input opened because MLTP pin has the pull-down resistor.

OE clock output enable

OE	Status	Remarks
L	Modulation clock output (OUT pin) Hi-Z/Power down status	_
Н	Operation status	Default

Note: When OE pin is set to "L", all oscillation circuits/PLL stop and enter power down mode, low-power consumption mode. Modulation clock output (OUT pin) becomes Hi-Z state during the power down. Set OE pin to "H" for input opened because OE pin has the pull-up resistor.

SPRD modulation type setting

SPRD	Modulation type	Remarks
L	Center spread	_
Н	Down spread	Default

Note: Set SPRD pin to "H" for input opened because SPRD pin has the pull-up resistor.

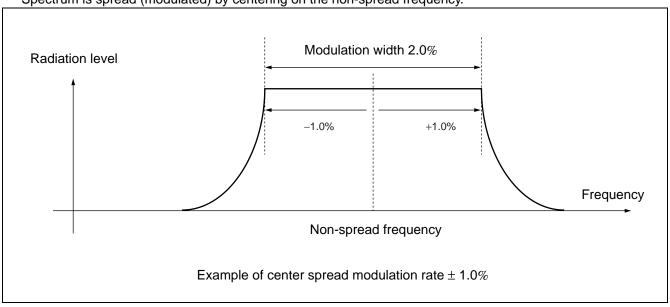
S0/S1 modulation rate setting

S1	S0	Modula	Remarks		
31	30	At down spread At center spread		- iveillal KS	
L	L	No modulation	No modulation	_	
L	Н	- 1.0%	± 0.5%	_	
Н	L	- 2.0%	± 1.0%	_	
Н	Н	- 4.0%	± 2.0%	Default	

Note: Set S1 and S0 pins to "H" for input opened because the pins have the pull-up resistor.

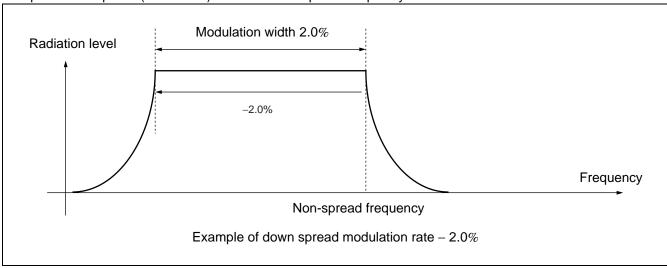
• Center spread

Spectrum is spread (modulated) by centering on the non-spread frequency.



• Down spread

Spectrum is spread (modulated) below the non-spread frequency.

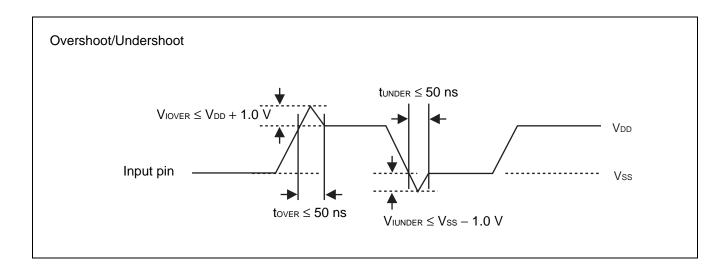


■ ABSOLUTE MAXIMUM RATINGS

Doromotor	Cumbal	Rating			
Parameter	Symbol	Min	Max	Unit	
Power supply voltage*	V_{DD}	- 0.5	+ 4.0	V	
Input voltage*	Vı	Vss - 0.5	V _{DD} + 0.5	V	
Output voltage*	Vo	Vss - 0.5	V _{DD} + 0.5	V	
Storage temperature	Тѕт	– 55	+ 125	°C	
Operation junction temperature	TJ	- 40	+ 125	°C	
Output current	lo	- 14	+ 14	mA	
Overshoot	Viover	_	$V_{DD} + 1.0 \text{ (tover} \le 50 \text{ ns)}$	V	
Undershoot	Viunder	Vss-1.0 (tunder ≤ 50 ns)	_	V	

^{* :} The parameter is based on Vss = 0.0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



■ RECOMMENDED OPERATING CONDITIONS

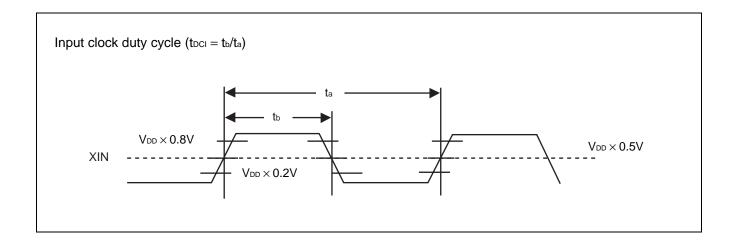
(Vss = 0.0 V)

Parameter	Symbol	Din	Pin Conditions		Value			
Parameter	Syllibol	FIII	Conditions	Min	Тур	Max	Unit	
Power supply voltage	V _{DD}	V_{DD}	At MLTP = "L"	2.7	3.3	3.6	V	
Trower supply voltage	Power supply voltage VDD		At MLTP = "H"	3.0	3.3	3.6	v	
"H" level input voltage	ViH	XIN, MLTP, OE, SPRD,	_	$V_{\text{DD}}\times0.80$		V _{DD} + 0.3	V	
"L" level input voltage	VıL	S1, S0	_	Vss	_	$V_{\text{DD}} \times 0.20$	V	
Input clock duty cycle	t DCI	XIN	Input frequency 12 MHz to 42 MHz	40	50	60	%	
Operating temperature	Та	_	_	- 40	_	+ 85	°C	

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.



■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

(Ta = -40 °C to +85 °C, V_{DD} = 2.7 V to 3.6 V, V_{SS} = 0.0 V)

Damamatan	Councile of	D:	O a maliti a ma		Value		Unit
Parameter	Symbol	Pin	Conditions	Min	Тур	Max	Unit
Power supply current	Icc	V _{DD}	24 MHz output no load capacitance	_	7.0	11.0	mA
Power down current	I PD	V _{DD}	At power down (At OE="L")	_	5	20	μΑ
Output voltage	Vон	OUT	"H" level output, Іон= – 8 mA	$0.8 \times V_{DD}$	_	V _{DD}	V
Output voltage	Vol	0	"L" level output, loL = 8 mA	Vss	_	$0.2 \times V_{DD}$	V
Output improduces	Zoc	OUT	MLTP = L, 12 MHz to 28 MHz output, V _{DD} = 2.7 V to 3.6 V	_	30		Ω
Output impedance	Zoc	001	MLTP = H, 80 MHz to 168 MHz output, VDD = 3.0 V to 3.6 V	_	20	_	Ω
Load capacitance	CL	OUT	MLTP = L, 12 MHz to 28 MHz output, V _{DD} = 2.7 V to 3.6 V	_	_	15	pF
Load capacitance	CL	001	MLTP = H, 80 MHz to 168 MHz output, VDD = 3.0 V to 3.6 V	_		15	pF
Built-in oscillation stabilization capacitance	Cosc	XIN, XOUT	_	_	4	_	pF
	R РИОЕН	OE	$V_{IH} = 0.8 \times V_{DD}$	10	25	100	kΩ
Input pull-up resistance	RPUOEL	OE	V _{IL} = 0.0 V	500	800	1200	kΩ
pat pail up rodictation	Rpu	SPRD, S1, S0	V1L = 0.0 V	25	50	200	kΩ
Input pull-down resistance	R _{PD}	MLTP	$V_{IH} = V_{DD}$	25	50	200	kΩ

Note: When OE pin is set to "L", the pull-up resistor connected to SPRD pin, S1 pin, and S0 pin and the pull-down resistor connected to MLTP pin are disconnected, and internal signal is fixed to "L". See "■ I/O CIRCUIT TYPE" for details.

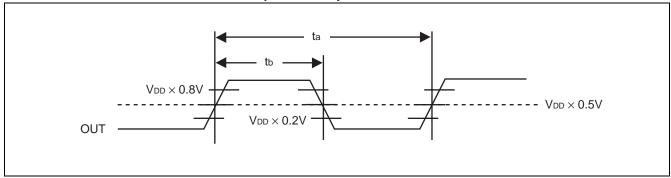
AC Characteristics

(Ta = -40 °C to +85 °C, $V_{DD} = 2.7$ V to 3.6 V, $V_{SS} = 0.0$ V)

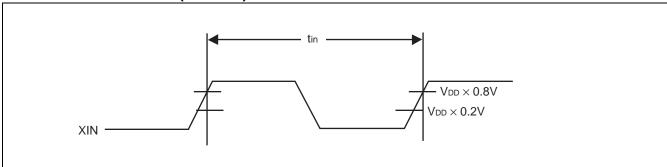
_ ,		5.	0 1111		Value		I Imit
Parameter	Symbol	Pin	Conditions	Min	Тур	Max	Unit
Input frequency	fin	XIN	MLTP= "L", V _{DD} = 2.7 V to 3.6 V, Crystal oscillation input	12	_	28	- MHz
Imput nequency	lin	XIIV	MLTP= "H", V _{DD} = 3.0 V to 3.6 V, Crystal oscillation input	20	_	42	IVII IZ
Crystal oscillation	fx	XIN,	Fundamental oscillation, MLTP= "L", VDD = 2.7 V to 3.6 V	12	_	28	- MHz
frequency	lx	XOUT	Fundamental oscillation, MLTP= "H", V _{DD} = 3.0 V to 3.6 V	20	_	42	- IVITIZ
Output frequency	fоит	OUT	MLTP= "L", V _{DD} = 2.7 V to 3.6 V	12	_	28	MHz
Output frequency	1001	001	MLTP= "H", V _{DD} = 3.0 V to 3.6 V	80	_	168	- IVII IZ
Output clock rise time	tr	OUT	0.2 × V _{DD} to 0.8 × V _{DD} Load capacitance 15 pF	0.4	_	4.0	ns
Output clock fall time	tf	OUT	0.2 × V _{DD} to 0.8 × V _{DD} Load capacitance 15 pF	0.4	_	4.0	ns
Output clock duty cycle	tocc	OUT	$0.5 \times V_{DD}$	40		60	%
Modulation frequency	fмор	OUT	Input frequency at 24MHz, MLTP = "L"	_	32.0	_	- kHz
iniodulation frequency	IMOD	001	Input frequency at 24MHz, MLTP = "H"		21.3	_	KIIZ
Lock-Up time	t LK	OUT	_	_	4	10	ms
Cycle-Cycle jitter	tuc	OUT	Ta= + 25°C, V _{DD} =3.3V, No load capacitance, Standard deviation σ	_	_	100	ps
Output enable "L" width	toelw	OE	_	1	_	_	μs
Dower cumply rice time	t	V _{DD}	MLTP= L, 0.0 V to 2.7 V	100	_	_	
Power supply rise time	t vdr	טט ע	MLTP= H, 0.0 V to 3.0 V	100	_	_	μs
Output Hi-Z start time after power down entry	t PEZ	OUT	Rise time or fall time of "OE" at 5 ns	_	_	10	ns
Output Hi-Z release time after power down exit	t PIZ	OUT	Rise time or fall time of "OE" at 5 ns	0	_	_	ns
Output start time after power down exit	t PIO	OUT	Rise time or fall time of "OE" at 5 ns Load capacitance 15 pF		_	10	ns

Note: The stabilization wait time of the modulation clock is required after the power is turned on or when the clock output enable setting (OE pin), multiplication setting (MLTP pin) or modulation rate setting (S1 pin and S0 pin) is changed. The stabilization wait time of the modulation clock takes the maximum value of Lock-Up time.

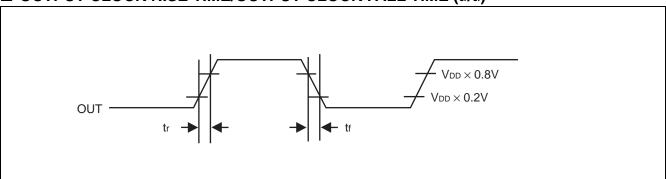
■ OUTPUT CLOCK DUTY CYCLE (tDCC = tb/ta)



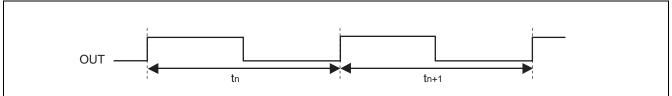
■ INPUT FREQUENCY (fin = 1/tin)



■ OUTPUT CLOCK RISE TIME/OUTPUT CLOCK FALL TIME (t_r/t_f)

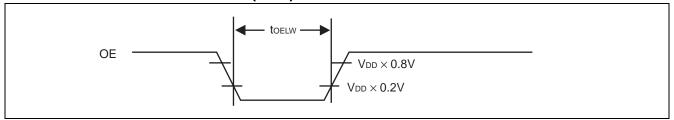


$\blacksquare \ \ \text{CYCLE-CYCLE JITTER (} \ \text{$t_{\text{JC}} = |\ t_{\text{n}} - t_{\text{n+1}}|$})$

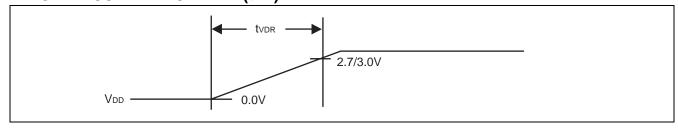


Note: Cycle-cycle jitter indicates the difference between a certain cycle and the immediately succeeding (or preceding) cycle.

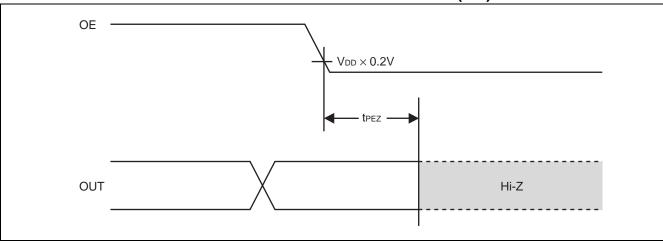
■ OUTPUT ENABLE "L" WIDTH (toELw)



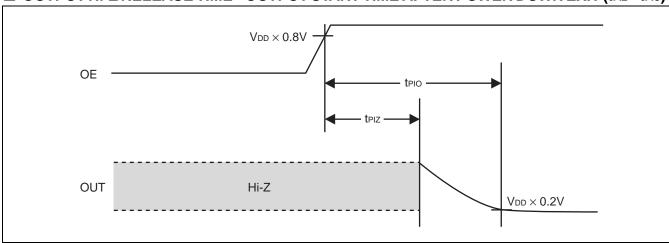
■ POWER SUPPLY RISE TIME (tvdr)



■ OUTPUT Hi-Z START TIME AFTER POWER DOWN ENTRY (tpez)

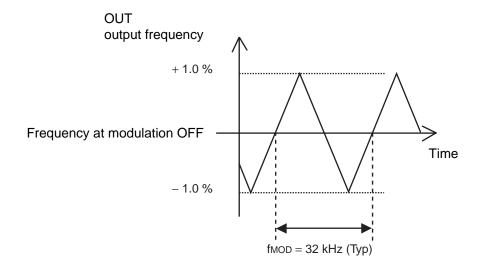


■ OUTPUT Hi-Z RELEASE TIME • OUTPUT START TIME AFTER POWER DOWN EXIT (tpiz • tpio)

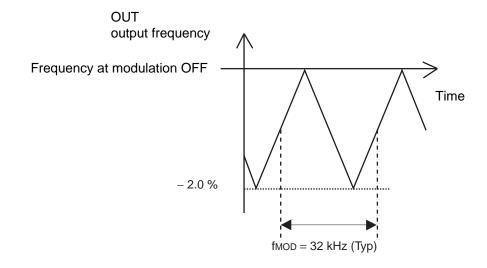


■ MODULATION WAVEFORM

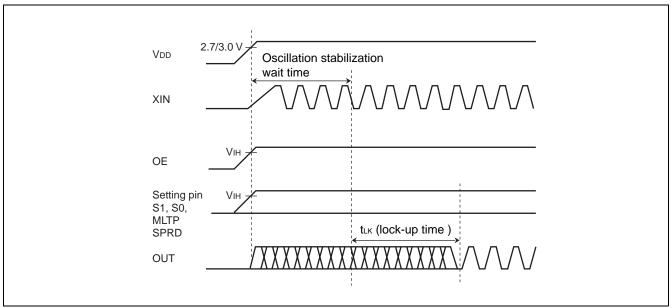
• Modulation rate ±1.0%, example of center spread



• Modulation rate -2.0%, example of down spread



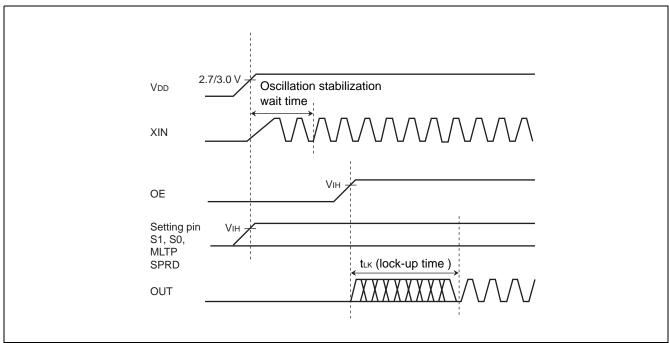
■ LOCK-UP TIME



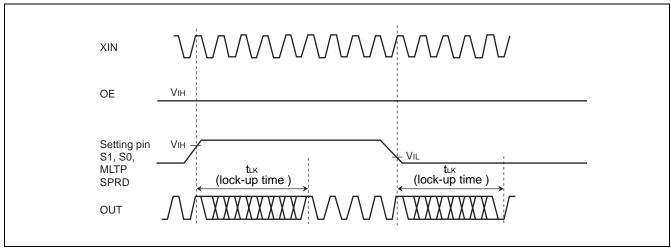
The clock oscillation stabilization wait time is required when the power is turned on.

If the OE pin is fixed at "H" level, the maximum time after the power is turned on until the required clock is obtained is (the oscillation stabilization wait time of input clock to XIN pin) + (the lock-up time "tlk").

For the stabilization wait time of input clock to the XIN pin, check the characteristics of the resonator or oscillator used.



If the OE pin is used for power down control, the required clock is obtained at most the lock-up time "t∟κ" after the OE pin goes "H" level.

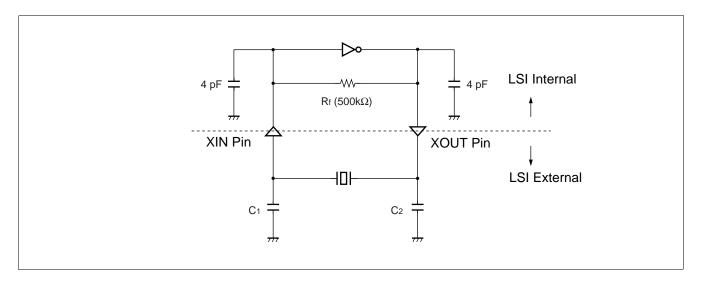


If the setting pin (S1, S0, MLTP, or SPRD) is used for control during normal operation, the required clock is obtained at most the lock-up time "tlk" after the level at the pin is determined.

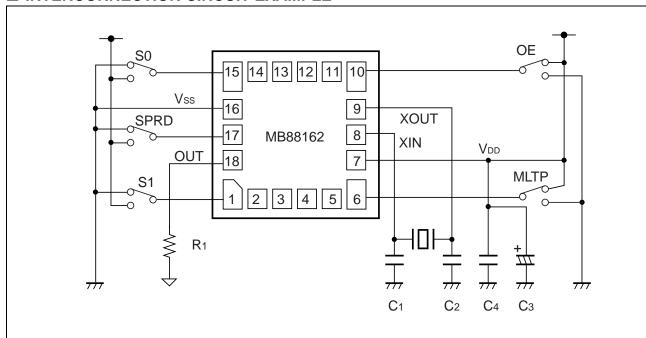
Note: The wait time for the clock signal output from the OUT pin to become stable is required after the IC is released from power-down mode by the OE pin or after another pin's setting is changed. During the period until the output clock signal becomes stable, the output frequency, output clock duty cycle, modulation period, and Cycle-Cycle jitter characteristic cannot be guaranteed. It is therefore advisable to perform processing such as cancelling a reset of the device at the succeeding stage after the lock-up time.

■ CRYSTAL OSCILLATION CIRCUIT

The figure below shows the connection example about general crystal resonator. The oscillation circuit has the built-in feedback resistor $(500 k\Omega)$ and oscillation stabilization capacitance $(4 \, pF)$. Because the value of oscillation stabilization capacitance must be adjusted to the most suitable value of the individual oscillator, add the capacitance (C1 and C2) to LSI external if necessary.



■ INTERCONNECTION CIRCUIT EXAMPLE



C₁, C₂ : Oscillation stabilization capacitance (see "■ CRYSTAL OSCILLATION CIRCUIT".)

 C_3 : Capacitor of 10 μF or higher

C₄ : Capacitor of about 0.01 μF (connect a capacitor of good high frequency property (ex.

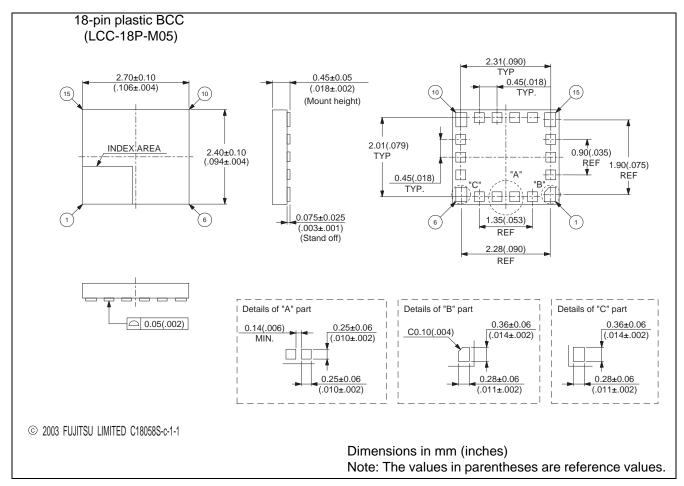
laminated ceramic capacitor) to close to this device)

R₁ : Impedance matching resistor for board pattern

■ ORDERING INFORMATION

Part no.	Package	Emboss taping
MB88162PVB-G-EFE1	18-pin plastic BCC	EF type
MB88162PVB-G-ERE1	(LCC-18P-M05)	ER type

■ PACKAGE DIMENSION



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